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(54) SPUTTERING TARGET MATERIAL FOR FORMING THIN FILM, THIN FILM, ELECTRODE-WIRED LAYER, OPTICAL RECORDING MEDIUM, ELECTRONIC COMPONENT, OPTOELECTRONIC COMPONENT AND ELECTRONIC DEVICE

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a sputtering target material for forming a thin film, which improves manufacturing easiness in a step of manufacturing an alloy, and stability and simplicity in a sputtering step when using it for a sputtering target.

SOLUTION: The sputtering target material for forming the thin film is made of a metallic material including Ag as a main component and 0.1-3.0 wt.% Mo. The use of such a sputtering target material for forming the thin film solves the problems in a prior art, and realizes a technology having various superior characteristics as the components of the various electronic components, electronic devices, optoelectronic components and optical recording media, while utilizing the advantages of Ag.

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